	Application No.	Applicant(s)	
Notice of Allowability	10/619,114 Examiner	SHEU ET AL. Art Unit	
	William M. Brewster	2823	
The MAILING DATE of this communication apperation apperation allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication GHTS. This application is subject t	pplication. If not include n will be mailed in due	ed course. THIS
1. This communication is responsive to <u>5 August 2005</u> .			•
2. The allowed claim(s) is/are <u>26-45</u> .			
3. \boxtimes The drawings filed on <u>14 September 2003</u> are accepted by	the Examiner.		
4.			
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. ☐ Notice of Informal F 6. ☑ Interview Summary Paper No./Mail Da 7. ☑ Examiner's Amend 8. ☑ Examiner's Statem 9. ☐ Other	/ (PTO-413), ate <u>082905</u> . ment/Comment	.'

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Daniel R. McClure on 2 September 2005.

The application has been amended as follows:

a) In the Claims:

In claim 26, line 10, delete, "and is formed by an angled implant of indium ions" In claim 37, lines 12-13, delete, "by performing an angled implant of indium ions" Cancel claims 46-47.

Reasons for Allowances

The following is an examiner's statement of reasons for allowance: claim 37, lines 4-13, the features of shallow trench with oxide liner, an insulator layer formed on said oxide liner that fills said shallow trench and extends to a level that is above the top of said substrate; active area and gate dielectric layer between the trenches, patterned gate layer formed on said gate dielectric layer wherein said gate layer extends over said adjacent shallow trenches; wherein said active area having an indium doped region that is adjacent to top corners of said shallow trenches and extends under part of gate dielectric layer, cannot be reasonably combined from the prior art of record.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to William M. Brewster whose telephone number is 571-272-1854. The examiner can normally be reached on Full Time.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

William M. Brewster

2 September 2005 WB